. Q HQT CTF QNVCI G CPF NGCMCI G E TTGPV

. Q KPF EVCPEG RCEMCI G

KK J U TI G E TTGPVECRCDKKKV

(KGNF U RRN HQT O QVQTU

. KPG TGEVKKKGTU HQT VTCPUKUVQTK GF O QVQTEQPVTQNNGTU

0 QP EQPVTQNNCDNG TGEVKKKGTU HQT EQP GTVGT

" 6

" 6 PNGUU QVJGT KJG URGEKKGF

(QT CTF QNVCI G	+ 6 L ℃	8 (				8
4 G GTUG NGCMCI GE TTGPV	8 4 8 44 / 6 L ℃	+ 44 /				O
	8 4 8 44 / 6 L ℃					O
6 J TGUJ QNF QNVCI G	(QTRQ GTNQUU ECNE NCVKQP QPN 6 L ℃	8 61				8
PCO KE TGUKJVCPEG		T 6				O

" 6 PNGUU QVJGT KJG URGEKKGF

6 J GTO CNKO RGF CPEG L PEVKQP VQ ECUG	RGTF KQF G	4 VJ LE				-
/ Q PVKPI VQTS G	CUG RNCVG VQ J GCVJKPM UETG /	/				0 O
	NGEVTQF G VQ VGTO KPCN UETG /					0 O

, / 6	, / 6		I 2 5	2 5	2 5

FIG.1: Forward characteristics(per diode)

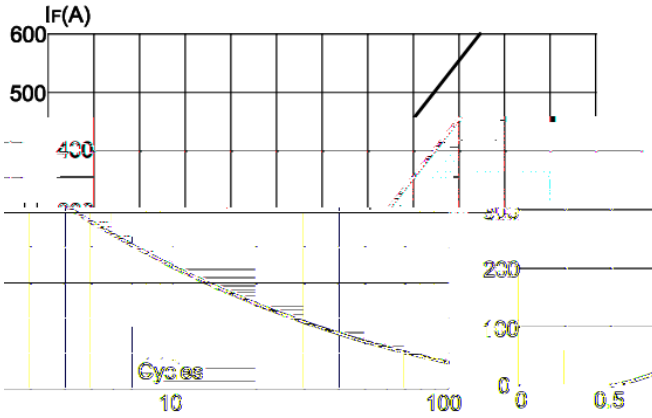
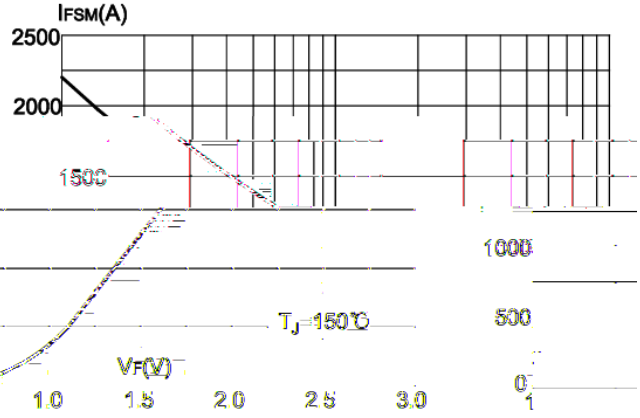


FIG.2: Peak on-state surge current



ximum transient thermal impedance
) Junction-to-case(per diode)

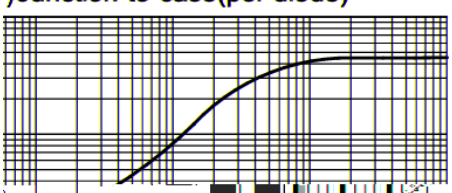
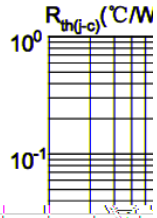
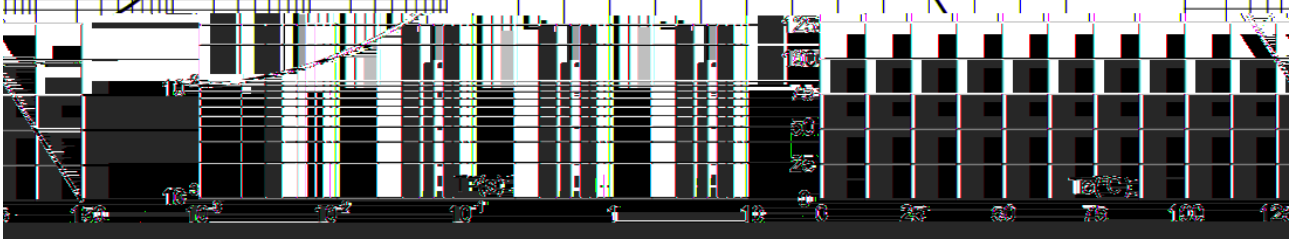


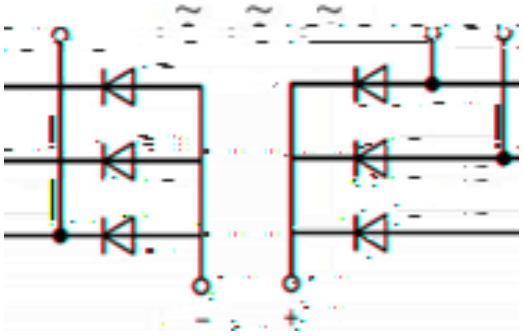
FIG.3: Forward current vs. case temperature

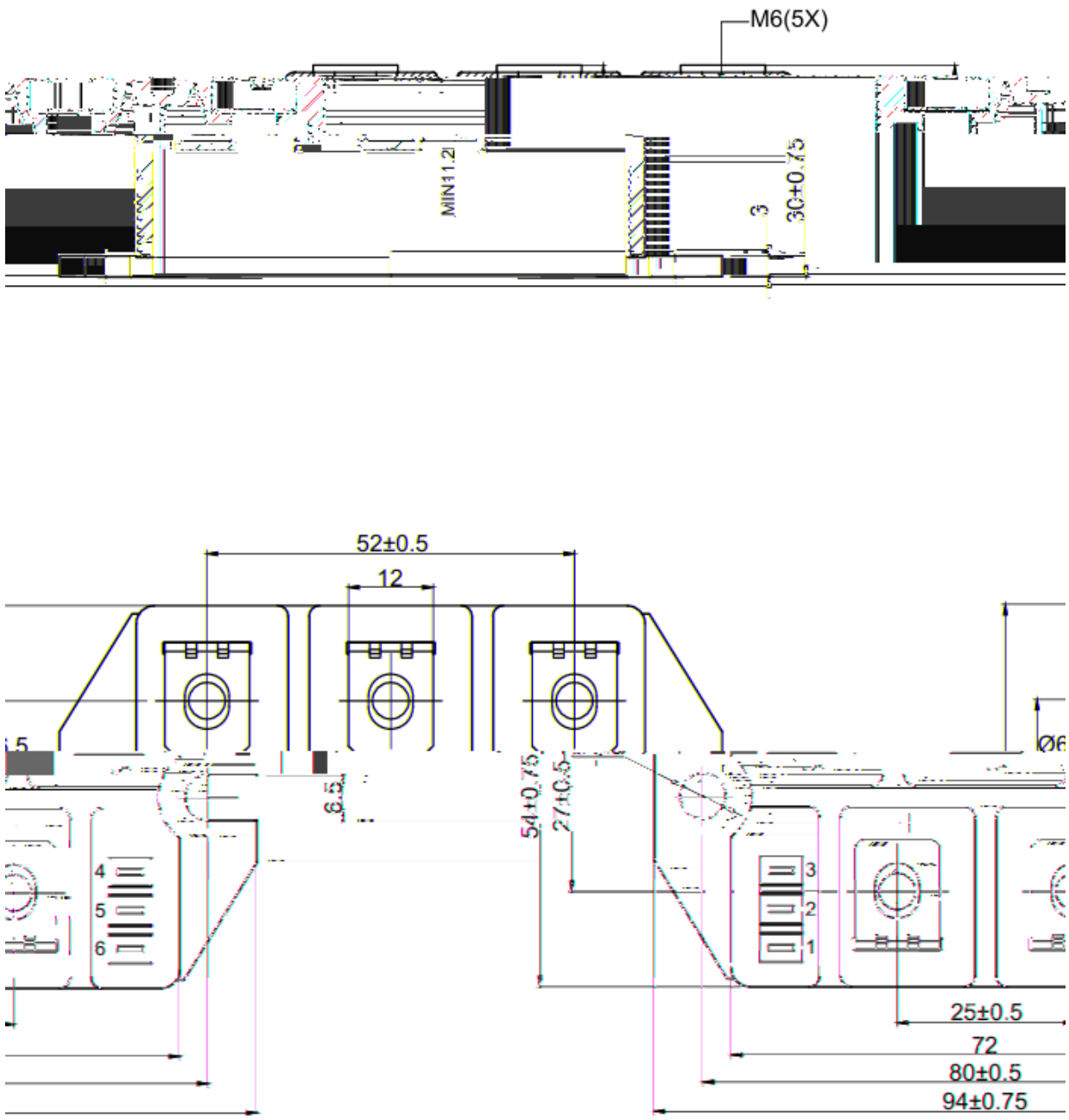


FIG.4: Ma









7 PKVQHOGCU TGOGPV OO